

FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

Applicant(s): Allen et al.
 Docket No.: YOR920030175US1
 Serial No.: 10/661,041
 Filing Date: September 12, 2003
 Group: 2811



U.S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE	IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313		

FOREIGN PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION	YES	NO

OTHER DOCUMENTS

EXAMINER	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.

Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).

Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).

DellaGuardia et al., "193 Lithography and RELACSTM Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).

Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).

Satou et al., "Sub-0.10 μ m Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

Examiner

D-06-05

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.